



## SEMINARIO

### **Magnetotransport properties of a graphite microwire produced by He<sup>+</sup> bombardment and embedded in a diamond crystal**

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We have investigated the magnetotransport properties of a graphite microwire (GM) embedded in a diamond crystal in the temperature range of 2 K to 300 K and magnetic field to  $\pm 8$  T. The GM was produced at  $\approx 3 \mu\text{m}$  below the surface of a diamond crystal through the implantation of He<sup>+</sup> ions of 1.8 MeV energy using a microbeam. The initial wire was amorphous and was crystallized after heat treatment at  $T \approx 1475$  K. After a first annealing treatment the electrical transport at low temperatures is well described by a fluctuation-induced tunneling conductance model. The tunneling process occurs between the partially graphitized grains separated by nearly insulating thin amorphous regions. After a second annealing the transport mechanism changes to variable range hopping conduction. A finite magnetoresistance (MR) was observed at temperatures  $T < 250$  K, which can be well described by a semi-empirical model that takes into account a spin dependent scattering process. The appearance of the graphitic structure after annealing treatment was confirmed by confocal Raman spectroscopy.

**22 DE ABRIL. 12.00h.**  
**AULA DEL EDIFICIO I+D**